

<b>Form PTO-1449</b>  U.S. Department of Commerce Patent and Trademark Office  <b>INFORMATION DISCLOSURE STATEMENT          BY APPLICANT</b> (Use several sheets if necessary)		<b>ATTY DOCKET NO.</b> <b>10932-US</b>		<b>SERIAL NO.</b>  			
		<b>APPLICANT</b>  <b>Luc OUELLET et al.</b>					
		<b>FILING DATE</b>  		<b>GROUP</b>  			
<b>U.S. PATENT DOCUMENTS</b>							
*Exam. Inti.		Document Number	Date	Name	Class	Sub Class	Filing Date if Appropriate
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Sub Class	Translation Yes No
<b>OTHER DOCUMENTS (Including Author, title, Date, Pertinent Pages, Etc.)</b>							
<i>wn</i>		D.K.W. Lam, "Low temperature plasma chemical vapor deposition of silicon oxynitride thin-film waveguides", Applied Optics, Vol. 23, No. 16, August 15, 1984, pp. 2744-2746.					
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<i>wn</i>		K. Worhoff et al., "Plasma enhanced chemical vapor deposition silicon oxynitride optimized for application in integrated optics", Sensor and Actuators, 74, 1999, pp. 9-12.					
<b>EXAMINER</b> <i>Wes Man</i>		<b>DATE CONSIDERED</b> <i>10/6/03</i>					
* Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Drawn line through citation, not in conformance and not considered. Include copy of this form with next communication to applicant.							

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<b>OTHER DOCUMENTS (Including Author, title, Date, Pertinent Pages, Etc.)</b>							
WA		A.J. Kenyon et al., "A luminescence study of silicon-rich silica and rare-earth doped silicon-rich silica", Electrochemical Society Proceedings Vol. 91-11, pp. 304-318.					
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wa		G. Grand et al., "Low-Loss PECVD Silica Channel Waveguides for Optical Communications", Electronic Letters, Vol. 26, No. 25, December 6 1990, pp. 2135-21-37.					
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<b>EXAMINER</b> [Signature]		<b>DATE CONSIDERED</b> 10/8/03					
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<b>TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT</b> (Under 37 CFR 1.97(b) or 1.97(c))			Docket No. 10932-US
In Re Application Of: Luc OUELLET, et al.			
Serial No. 09/833,711	Filing Date 13 April 2001	Examiner	Group Art Unit 2874
Title: OPTICAL QUALITY SILICA FILMS			
Address to: Assistant Commissioner for Patents Washington, D.C. 20231			
<b>37 CFR 1.97 (b)</b>			
1. <input checked="" type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application; within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or before the mailing date of a first Office Action on the merits, whichever event occurs last.			
<b>37 CFR 1.97 (c)</b>			
2. <input type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed after three months of the filing of a national application, or the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or after the mailing date of a first Office Action on the merits, whichever occurred last but before the mailing date of either:  1. a Final Action under 37 CFR 1.113, or  2. a Notice of Allowance under 37 CFR 1.311,  whichever occurs first.  Also submitted herewith is:  <input type="checkbox"/> a certification as specified in 37 CFR 1.97(e);  <b>OR</b>  <input type="checkbox"/> the fee set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under 37 CFR 1.97(c).			

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<b>TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT</b> (Under 37 CFR 1.97(b) or 1.97(c))	Docket No. 10932-US
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In Re Application Of: Luc OUELLET, et al.

Serial No. 09/833,711	Filing Date 13 April 2001	Examiner	Group Art Unit 2874
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Title: OPTICAL QUALITY SILICA FILMS

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(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

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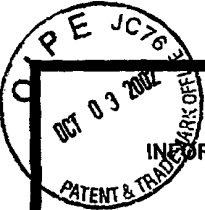
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APPLICANT(S)  
Luc OUELLET, et al.

FILING DATE  
13 April 2001

GROUP  
2874

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WM	4,394,401	July 19, 1983	Shioya et al.	427	39	August 7, 1981
	5,904,491	May 18, 1999	Ojha et al.	438	31	April 23, 1997
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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
WM	0 935 284 A1	8-1999	EP	—	—		
WM	0 624 660 A1	11-1994	EP	—	—		

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WM	(1) "Stress in PSG and nitride films as related to film properties and annealing", T.H. Tom Wu et al., Solid State Technology, 35 (1992), No. 5, pages 65-72.
WM	(2) "Characteristics of low-temperature and low-energy plasma-enhanced chemical vapor deposited SiO <sub>2</sub> ", J. Appl. Phys., Vol. 74, No. 4, 1993, pages 2638-2648.
WM	(3) "Plasma-activated deposition and properties of phosphosilicate glass film", Akira Takamatsu et al., Journal of the Electrochemical Society, 1984, Vol. 131 No. 8, pages 1865-1870. (4) "Controlled oxidation of silane", K. Strater, RCA Electronic Components, pages 618-629.

EXAMINER

Wes Mauer

DATE CONSIDERED

10/8/03

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